

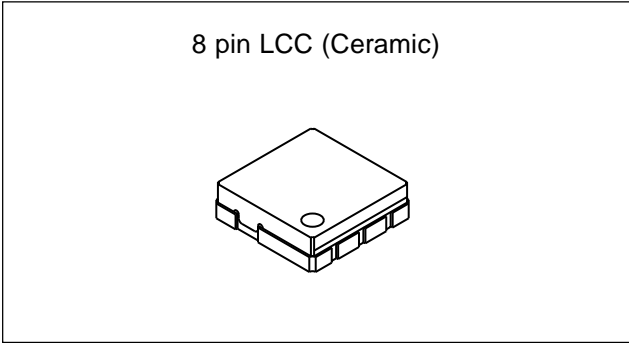
Power Amplifier Module for JCDMA

Description

The CXG1108K is the power amplifier module which operates at a single power supply. This IC is designed using the Sony's original p-Gate HFET process.

Features

- Single power supply operation:
 - $V_{DD1} = V_{DD2} = 3.5V$,
 - $V_{GG} = 2.95V$ (@High mode),
 - $V_{GG} = 2.7V$ (@Low mode)
- Ultrasmall package: 0.065cc (6.2mm × 6.2mm × 1.7mm)
- High efficiency: $\eta_{add} = 37.5\%$ (@900MHz, $P_{OUT} = 27dBm$)
- Output power (high/low mode switching supported):
 - $P_{OUT} \leq 17dBm$: Low mode ($V_{GG} = 2.7V$)
 - $P_{OUT} = 17$ to $27dBm$: High mode ($V_{GG} 2.95V$)
- Gain: $G_p = 26dB$ (@900MHz)



Applications

Power amplifier for JCDMA system cellular phones

Structure

p-Gate HFET module

Recommended Operating Conditions

$V_{DD} = 3.3$ to $4.2V$
 $V_{GG} = 2.95V \pm 1\%$ (High Mode)
 $2.7V \pm 1\%$ (Low Mode)

Absolute Maximum Ratings

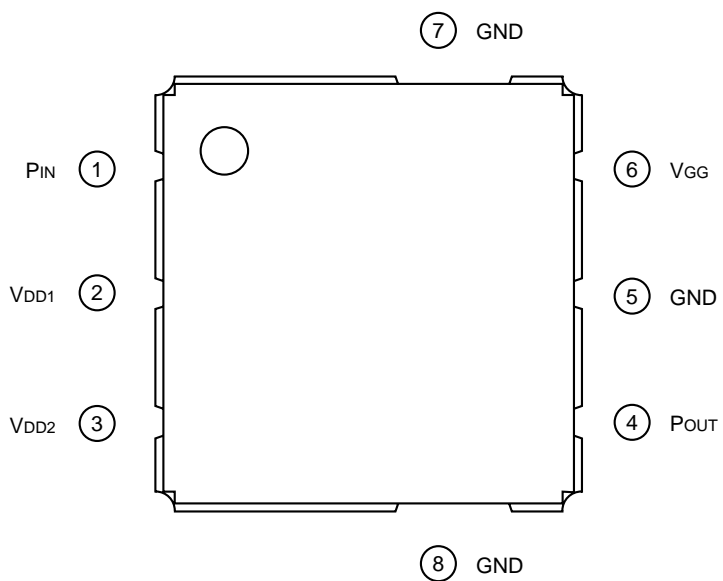
• Operating case temperature	T_{case}	-30 to +85	°C
• Storage temperature	T_{stg}	-30 to +125	°C
• Bias voltage	V_{DD1}, V_{DD2}	6	V
• Bias voltage	V_{GG}	3.3	V
		($V_{DD1} = V_{DD2} = 3.5V$)	
• Input power	P_{IN}	8	dBm

GaAs module is ESD sensitive devices. Special handling precautions are required.

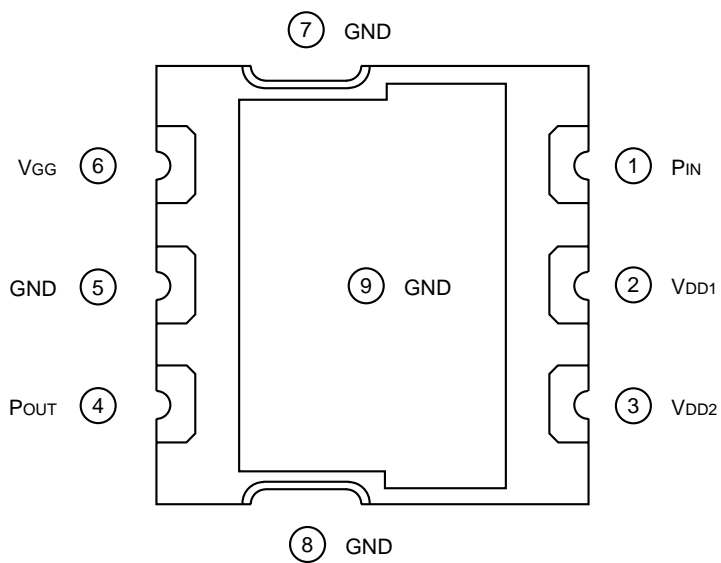
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package Outline/Pin Configuration

Front



Back

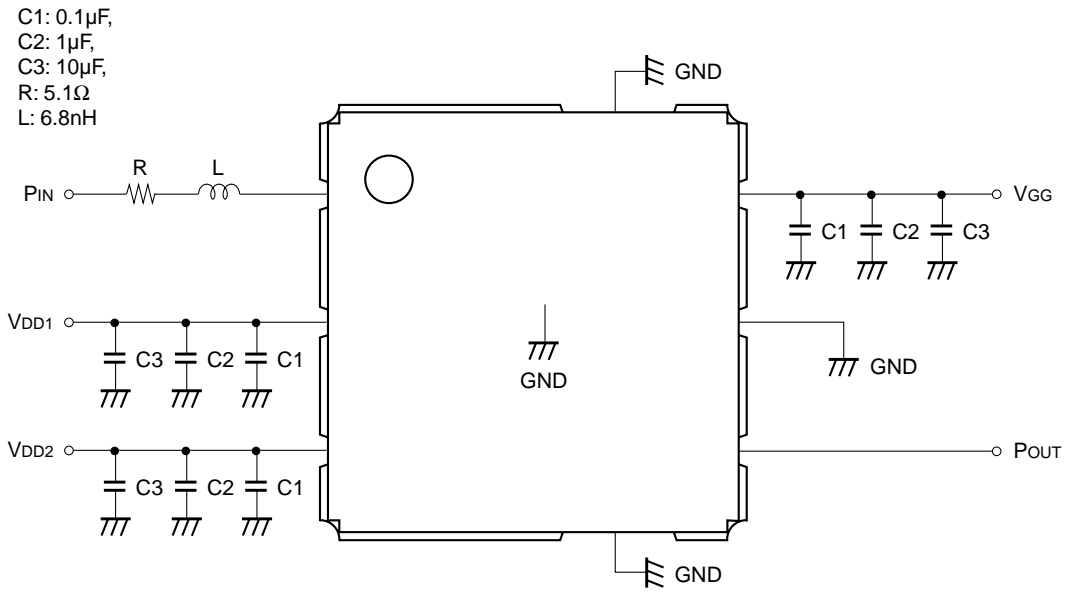


Electrical Characteristics

(ZS = ZL = 50Ω, IS-95 Modulation, Ta = 25°C)

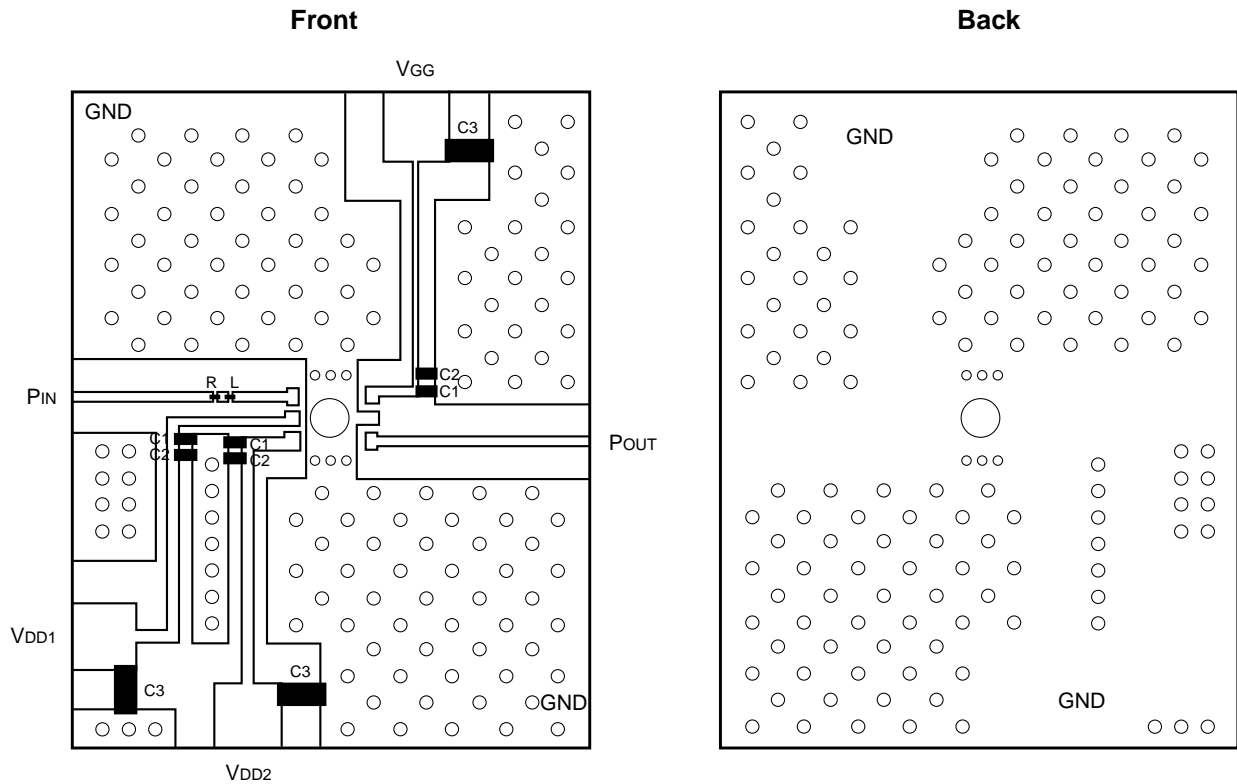
Item	Conditions	Min.	Typ.	Max.	Unit
Frequency		887		925	MHz
Current consumption 1	P _{OUT} = 27dBm, V _{DD} = 3.5V, V _{GG} = 2.95V		380	430	mA
Current consumption 2	P _{OUT} = 14dBm, V _{DD} = 3.5V, V _{GG} = 2.7V		110	130	mA
Gain	P _{OUT} = 27dBm, V _{DD} = 3.5V, V _{GG} = 2.95V	24	26	28	dB
ACPR1 (High mode)	P _{OUT} = 27dBm, V _{DD} = 3.5V, V _{GG} = 2.95V, ±900kHz offset, 30kHz band width		-51	-46	dBc
ACPR2 (High mode)	P _{OUT} = 27dBm, V _{DD} = 3.5V, V _{GG} = 2.95V, ±1.98MHz offset, 30kHz band width		-60	-57	dBc
ACPR1 (Low mode)	P _{OUT} = 17dBm, V _{DD} = 3.5V, V _{GG} = 2.7V, ±900kHz offset, 30kHz band width		-58	-46	dBc
ACPR2 (Low mode)	P _{OUT} = 17dBm, V _{DD} = 3.5V, V _{GG} = 2.7V, ±1.98MHz offset, 30kHz band width		-75	-57	dBc
2nd, 3rd harmonics	P _{OUT} = 27dBm, V _{DD} = 3.5V, V _{GG} = 2.95V		-40	-30	dBc
Input VSWR	V _{DD} = 3.5V, V _{GG} = 2.95V		1.3	2.5	
Gate current	V _{GG} = 2.95V, P _{OUT} ≤ 27dBm		2.5	5	mA
Gain deviation within band	P _{OUT} = 27dBm, V _{DD} = 3.5V, V _{GG} = 2.95V		1.2	2	dB

Recommended External Circuit



Recommended Evaluation Board

Board material: Glass fabric-base epoxy
 Size: 40mm \times 50mm \times 0.6mm
 Relative dielectric constant: 4.6



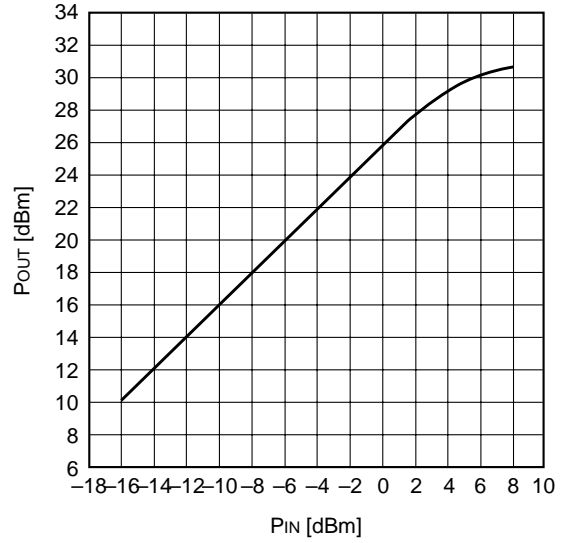
Example of Representative Characteristics

Conditions: $f = 900\text{MHz}$

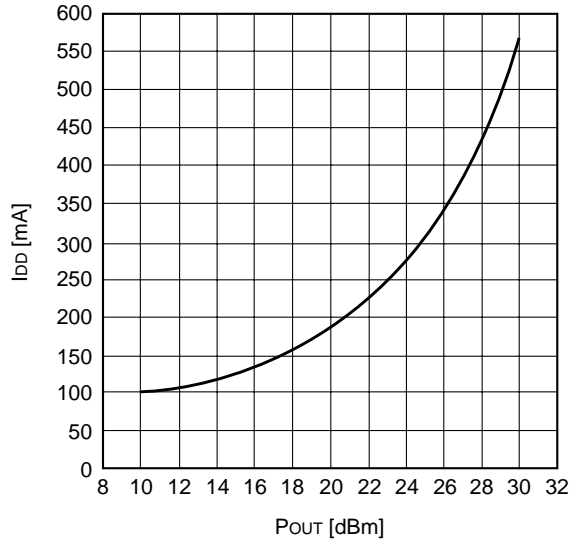
$V_{DD1} = V_{DD2} = 3.5\text{V}$, $V_{GG} = 2.95\text{V}$

$T_a = 25^\circ\text{C}$

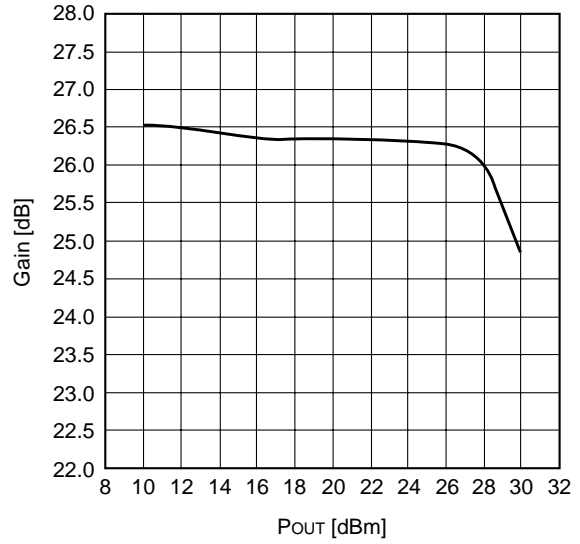
POUT vs. PIN



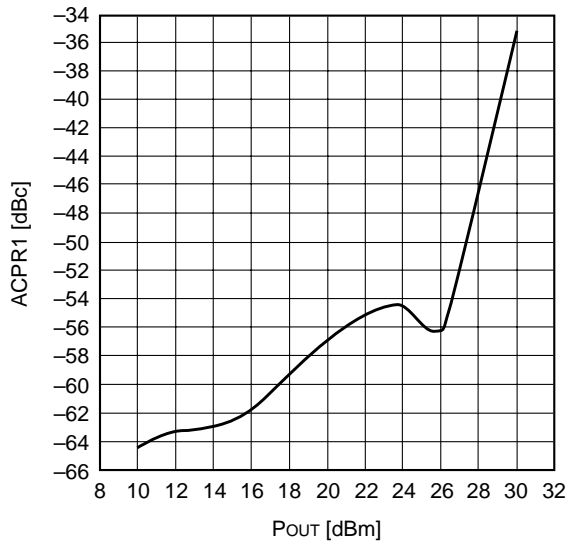
IDD vs. POUT



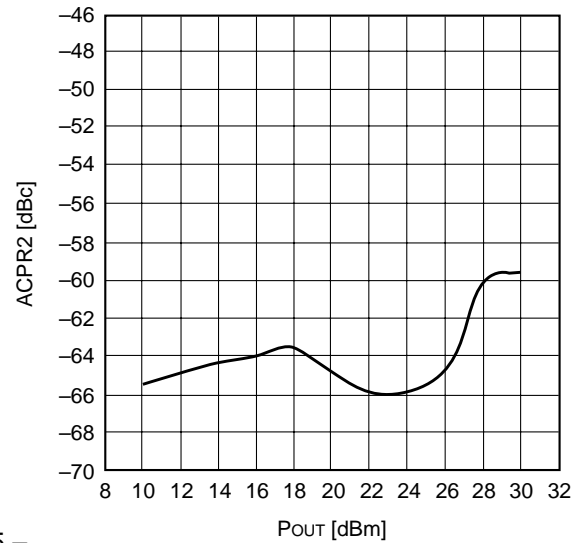
Gain vs. POUT



ACPR1 vs. POUT



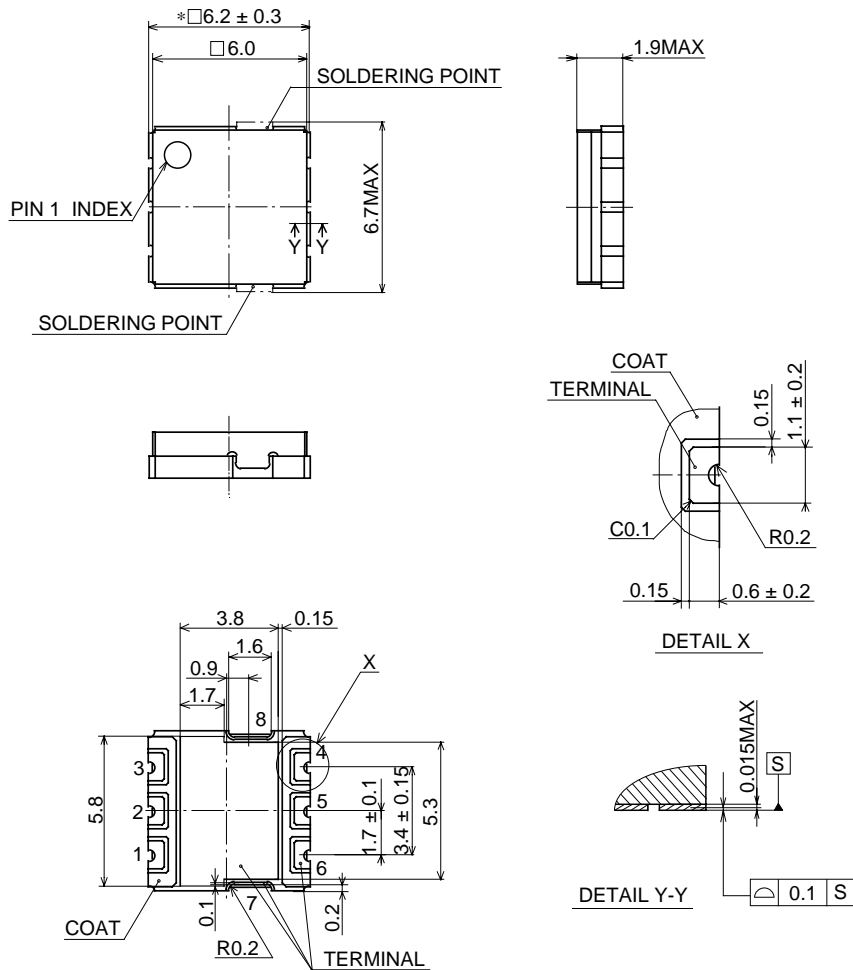
ACPR2 vs. POUT



Package Outline

Unit: mm

8PIN LCC (Ceramic)



Dimension " *"dose not include cutting burr.

SONY CODE	LCC-8C-601
EIAJ CODE	_____
JEDEC CODE	_____

PACKAGE STRUCTURE

PACKAGE MATERIAL	CERAMIC SUBSTRATE
TERMINAL TREATMENT	GOLD PLATING
TERMINAL MATERIAL	NICKEL PLATING
PACKAGE MASS	0.8g